1N5767 SERIES

KEY FEATURES

MICROSEMICONDUCTOR

- Useful attenuation from 1 μA to 100 mA bias
- Capacitance below 0.4 pF
- Low distortion in switches and attenuators
- Metallurgical bond
- Sealed in glass

American



The 1N5767 and the 1N5957 PIN diodes are based upon low capacitance PIN chips designed with long minority carrier lifetime, and thick intrinsic width. Thus operation as low as 1 MHz is possible with low distortion. Additionally, the low diode capacitance allows useful operation well into the microwave frequency range. The 1N5767 is a general purpose low power PIN diode designed for Both switch and attenuator applications. The 1N5957 is primarily used as an attenuator PIN diode and is particularly suitable wherever current controlled, wide dynamic range resistance elements are required. The 1N5957 has also been characterized for the 75 Ω attenuator, commonly employed in CATV systems.

ABSOLUTE MAXIMUM RATINGS AT 25 °C (unless otherwise specified)				
Reverse Voltage				
V_{R} (I _R = 10 µA)	100 V			
Average Power Dissipation: (25 °C)				
Free Air (P _A)	400 mW (Derate linearly to 175 °C)			
Operating and Storage				
Temperature Range	-65 °C to +175 °C			

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PARAMETER	SYMBOL	CONDITIONS	1N5767	1N5957	UNITS
Total Capacitance (Max)	CT	V _R = 100 V, F = 1 MHz	0.4	0.4	pF
Series Resistance	R _s	If = 10 μ A, F = 100 MHz	1000Ω (min) 2000Ω (typ)	1500Ω (min) 3000Ω (typ)	Ohms
Series Resistance	R _s	If = 20 mA, F = 100 MHz	8Ω (max) 4Ω (typ)	8Ω (max) 6Ω (typ)	Ohms
Series Resistance	R _s	lf = 100 mA, f = 100 MHz	2.5Ω (max) 1.5Ω (typ)	3.5Ω (max) 2.5Ω (typ)	Ohms
Carrier Lifetime	τ	I _F = 10 mA	1.0 (min)	1.5 (min) 2.0 (typ)	μS
Reverse Current	I _R	V_R = Voltage Rating	10 (max)	10 (max)	μA
Current for Rs = 75 Ω	I ₇₅	Rs = 75 Ω	0.7	0.8 – 1.2	mA
Return Loss	-	Diode terminates 75 Ω line	30 (typ)	30 (typ)	dB
Second Order Distortion	-	Bridged tee attenuator Attenuation = 10 dB	-40 (typ)	-50 (typ)	dB
Third Order Distortion	-	Pin = 50 dBmv F1 = 10 MHz F2 = 13 MHz	-60 (typ)	-65 (typ)	dB

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